

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	-2.5 -2.0	A
Maximum Continuous Body Diode Forward Current (Note 6)	I <sub>S</sub>	-1.0	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%) (Note 6)	I <sub>DM</sub>	-15	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	259	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	0.7	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	175	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.4	—	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	63	90	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1.5A
			83	120		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -1.2A
			160	180		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -1.2A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	335	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	72	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	32	—	pF	
Gate Resistance	R <sub>G</sub>	—	15.5	—	Ω	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1.0MHz
Total Gate Charge	Q <sub>g</sub>	—	3.5	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -4V, I <sub>D</sub> = -3.5A
Gate-Source Charge	Q <sub>gs</sub>	—	0.4	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	1.1	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	3.7	—	ns	V <sub>DS</sub> = -4V, V <sub>GS</sub> = -4.5V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>R</sub>	—	8.7	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	17.8	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	8	—	ns	I <sub>F</sub> = -4A, di/dt = 100A/μs
Reverse Recovery Time	t <sub>RR</sub>	—	9	—	ns	
Reverse Recovery Charge	Q <sub>RR</sub>	—	1.5	—	nC	I <sub>F</sub> = -4A, di/dt = 100A/μs

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
  - Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

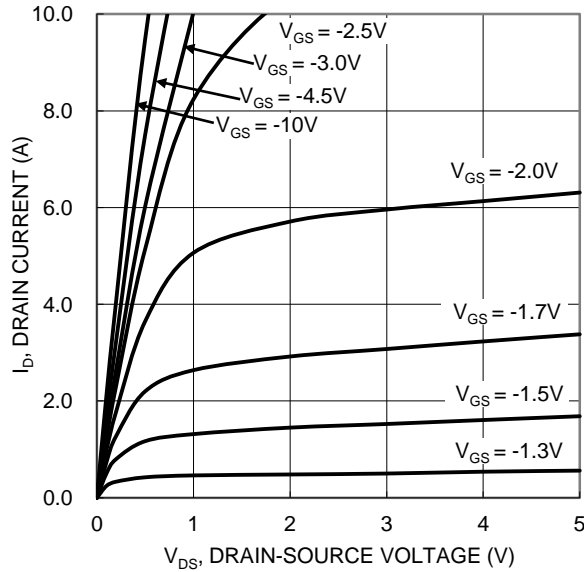


Figure 1. Typical Output Characteristic

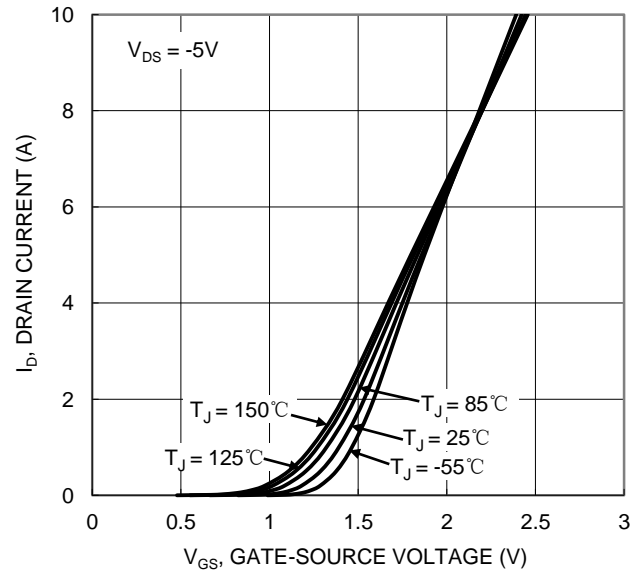


Figure 2. Typical Transfer Characteristic

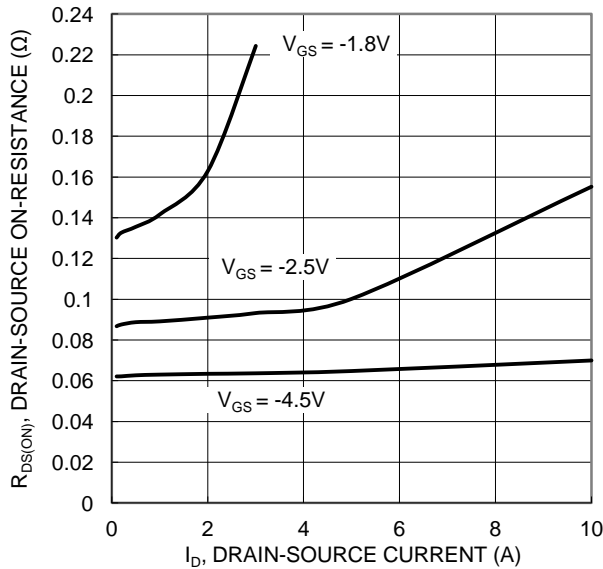


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

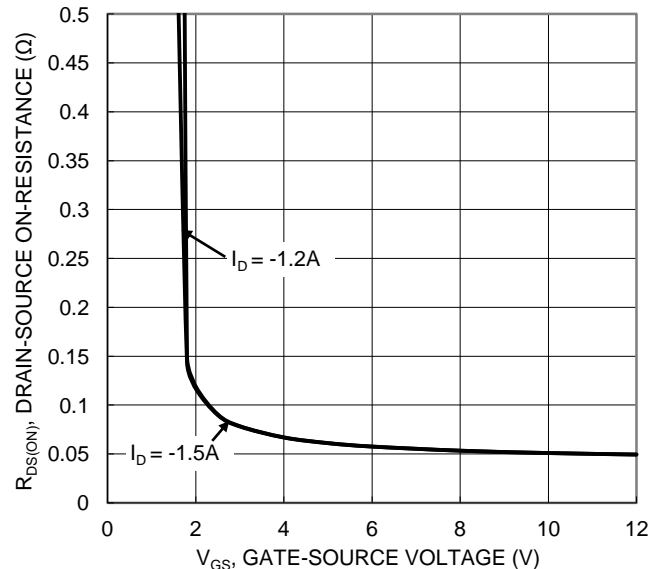


Figure 4. Typical Transfer Characteristic

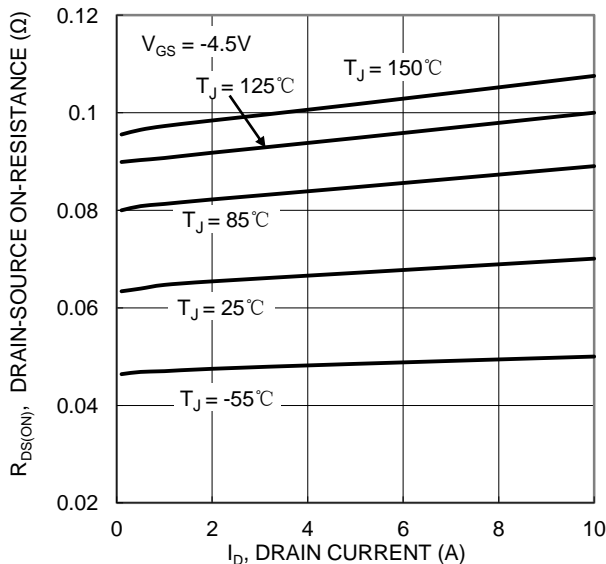


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

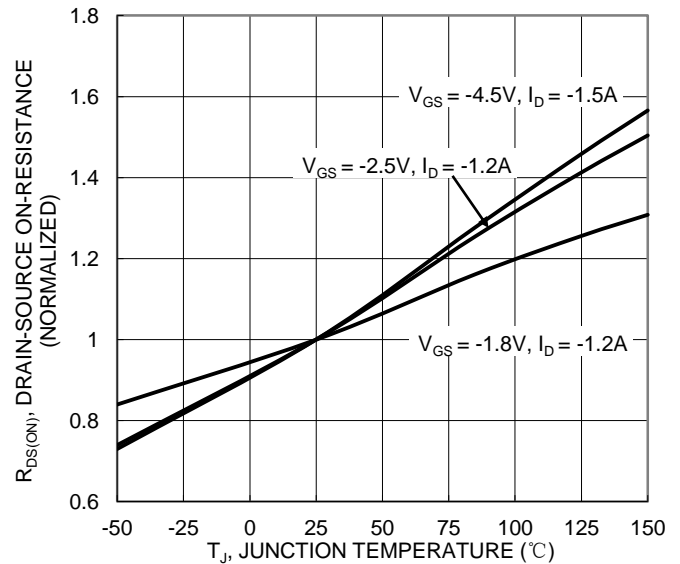
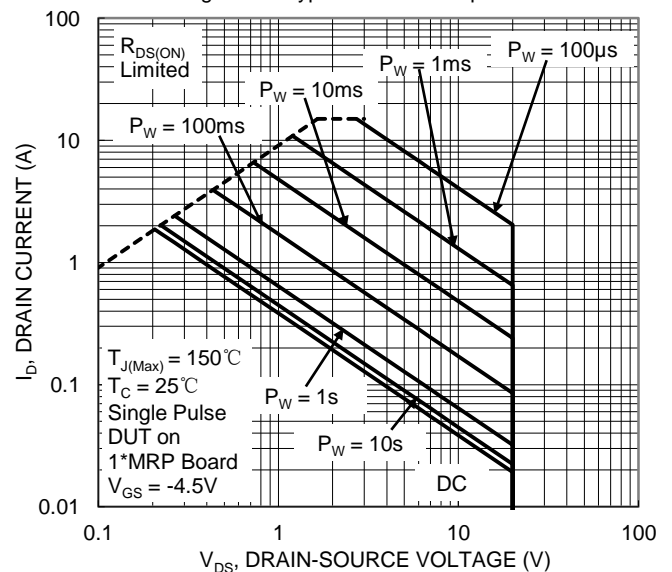
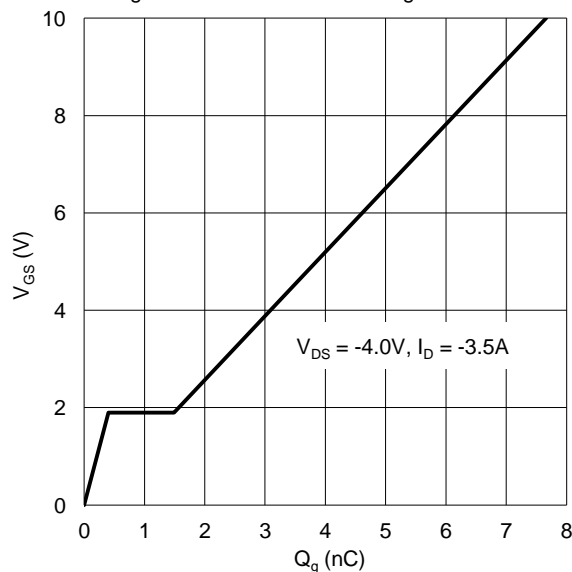
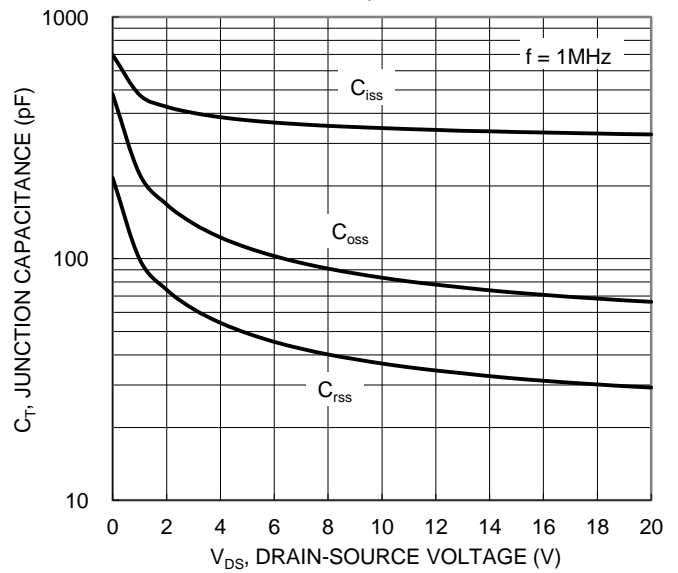
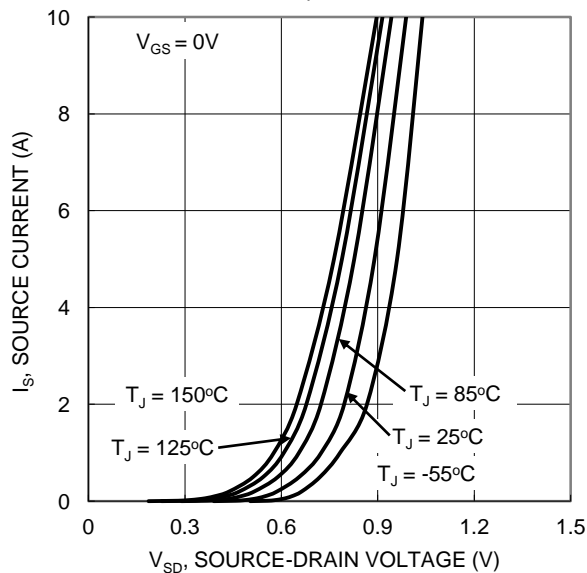
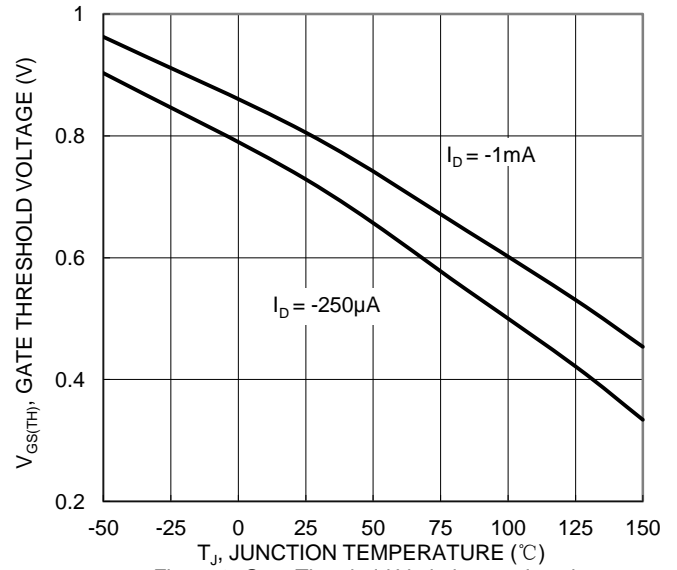
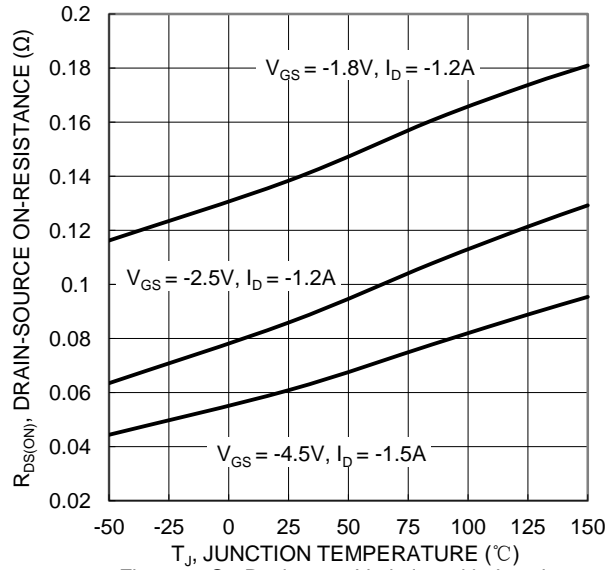


Figure 6. On-Resistance Variation with Junction Temperature



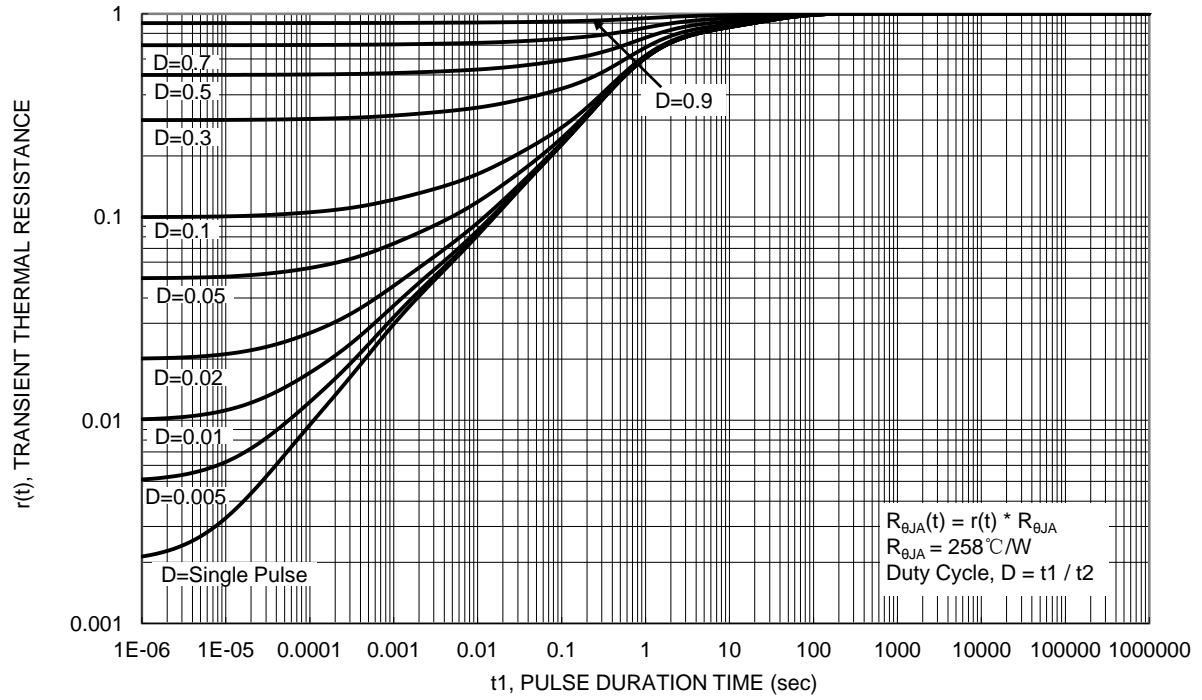
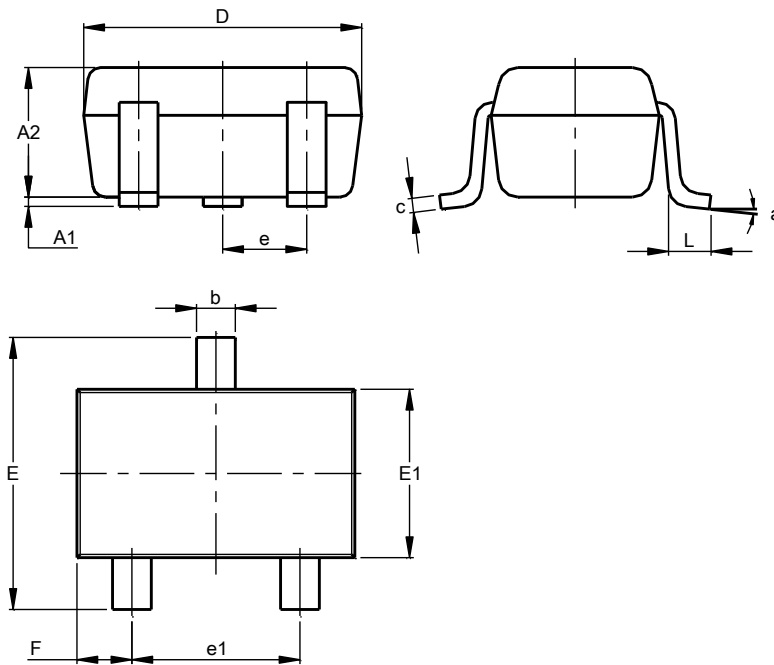


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT323

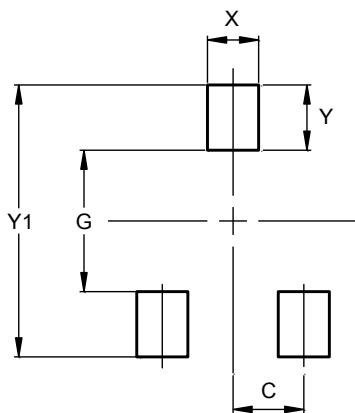


SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500

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